FEATURES

• High Gain at Low Current

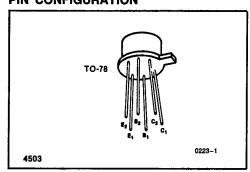
2N5117-2N5119

- Low Output Capacitance
- Good h_{FE} Match
- Tight V_{BE} Tracking
- Dielectrically Isolated Matched Pairs for Differential **Amplifiers**

General Purpose Amplifier

Dielectrically Isolated Dual PNP

PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted) Collector-Base or Collector-Emitter Emitter-Base Voltage (Notes 1 and 2) -7V Collector-Collector Voltage 100V Storage Temperature Range -65°C to +200°C Operating Temperature Range -55°C to +175°C Lead Temperature (Soldering, 10sec) +300°C

ONE SIDE BOTH SIDES Power Dissipation 250mW 500mW Derate above 25°C 1.67mW/°C 3.33mW/°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

TO-78
2N5117
2N5118
2N5119

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Symbol		Test Conditions			2N5117 2N5118		2N5119		Units
					Min	Max	Min	Max	
hfE	DC Current Gain	I _C =10μA, V _{CE} =5.0V			100	300	50		
		I _C =500μA, V _{CE} =5.0V			100		50		
		I _C =10μA, V _{CE} =5.0V, T _A =-55°C			30		20		
ICBO	Collector Cutoff-Current	I _E =0, V _{CB} =30V				0.1		0.1	nA
				T _A = 150°C		0.1		0.1	μΑ
EBO	Emitter Cutoff Current	I _C =0, V _{EB} =5.0V				0.1		0.1	nΑ
IC1-C2	Collector-Collector Leakage	V _{CC} =100V				5.0		5.0	pΑ
GBW	Current Gain Bandwith Product (Note 4)	I _C =500μA, V _{CE} =10V			100		100		MHz
Cob	Output Capacitance (Note 4)	I _E =0, V _{CB} =5.0V, f=1	MHz			0.8		8.0	
Cte	Emitter Transition Capacitance (Note 4)	I _C =0, V _{EB} =0.5V, f=1MHz				1.0		1.0	pF
C _{C1} -C ₂	Collector-Collector Capacitance (Note 4)	V _{CC} =0, f=1MHz				0.8		0.8	
V _{CEO(sust)}	Collector-Emitter Sustaining Voltage	I _C =1.0mA, I _B =0			45		45		٧
NF	Narrow Band Noise Figure (Note 4)	$I_C = 10 \mu A$, $V_{CE} = 5.0 V$ $f = 1 kHz$, $R_G = 10 k\Omega$ BW = 200Hz			4.0		4.0	dΒ	
BV _{CBO}	Collector Base Breakdown Voltage	I _C =10μΑ, I _E =0			45		45		v
BVEBQ	Emitter Base Breakdown Voltage	I _E =10μΑ, I _C =0			7.0		7.0	_	v

INTERSIL'S SOLE AND EXCLUSIVE WARRANTY OBLIGATION WITH RESPECT TO THIS PRODUCT SHALL BE THAT STATED IN THE WARRANTY ARTICLE OF THE CONDITION OF SALE.
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2N5117-2N5119

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SINTERSIL

MATCHING CHARACTERISTICS (T_A = 25°C unless otherwise specified)

T-29-27

Sumbal	Parameter	Test Conditions			2N5118		2N5119		Units
Symbol					Min	Max	Min	Max	
h _{FE1} /h _{FE2}	DC Current Gain Ratio	I _C = 10μA to 500μA, V _{CE} =5V I _C = 10μA, V _{CE} =5.0V							
	(Note 3)				0.85	1.0	0.8	1.0	
V _{BE1} -V _{BE2}	Base-Emitter Voltage	I _C =10μA to 500μA, V _{CE} =5V							mV
	Differential	I _C =10μA, V _{CE} =5.0V				5.0		5.0	
B1-1B2	Base Current Differential			10.0		15		40	nA
Δ(V _{BE1} -V _{BE2})/ΔΤ	Base Voltage Differential Change with Temperature	$T_A = -55^{\circ}\text{C to} + 125^{\circ}$	С	3.0		5.0		10	μV/°C
Δ(I _{B1} -I _{B2})/ΔΤ	Base-Current Differential Change with Temperature	T _A = -55°C to +125°		0.3		0.5		1.0	nA/°C

NOTES: 1. Per transistor.

For the transition.
 The reverse base-to-emitter voltage must never exceed 7.0 volts and the reverse base-to-emitter current must never exceed 10μA.
 Lower of two h_{FE} readings is defined as h_{FE}.
 For design reference only, not 100% tested.